Silicon P-Channel MOS FET

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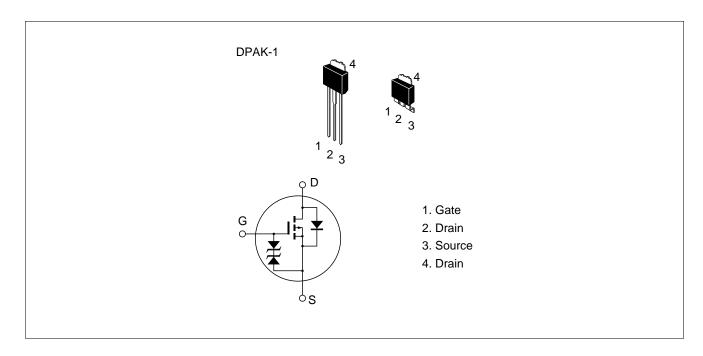
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter and ultrasonic power oscillators

Outline





Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

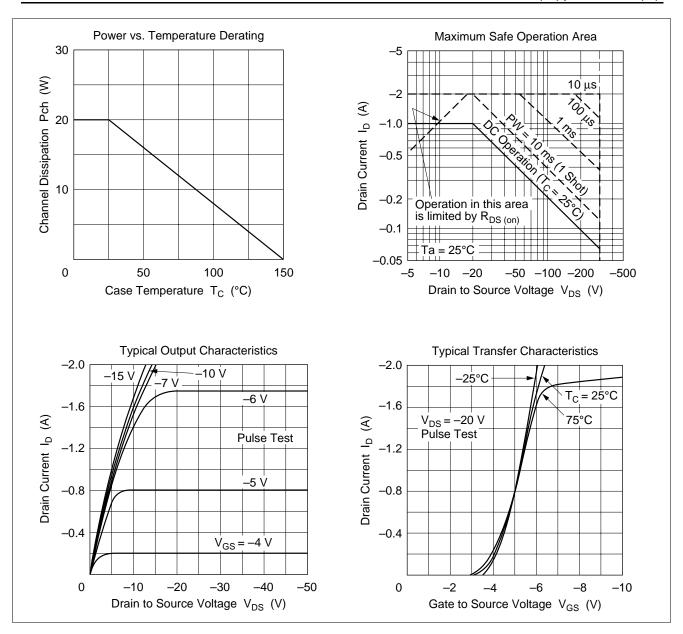
| Item | Symbol | Ratings | Unit |
|---|------------------------------|-------------|------|
| Drain to source voltage | $V_{\scriptscriptstyle DSS}$ | -300 | V |
| Gate to source voltage | $V_{\sf GSS}$ | ±20 | V |
| Drain current | I _D | -1 | A |
| Drain peak current | I D(pulse) | -2 | A |
| Body to drain diode reverse drain current | I _{DR} | -1 | A |
| Channel dissipation | Pch*1 | 20 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

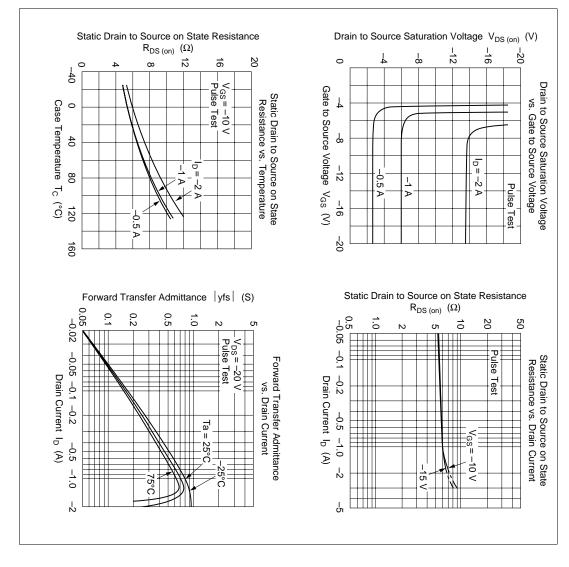
Note: 1. Value at $T_c = 25^{\circ}C$

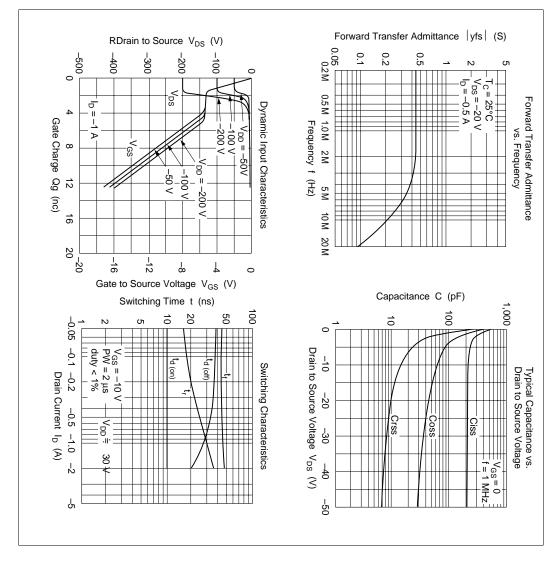
Electrical Characteristics ($Ta = 25^{\circ}C$)

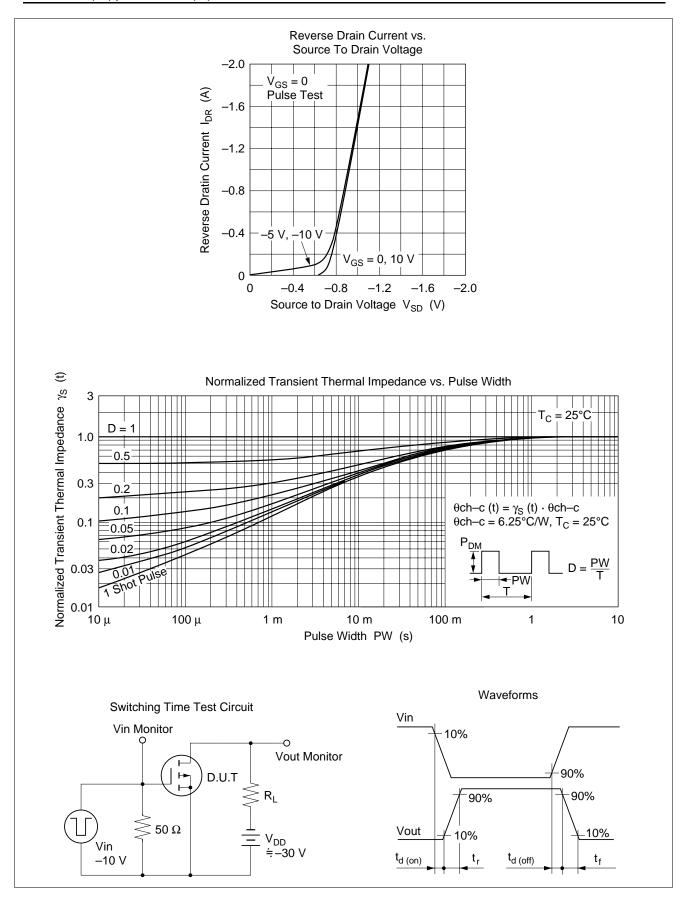
| Item | Symbol | Min | Тур | Max | Unit | Test conditions | |
|--|---------------------|------|------|------|------|---|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | -300 | _ | _ | V | $I_{D} = -10 \text{ mA}, V_{GS} = 0$ | |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±20 | _ | _ | V | $I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$ | |
| Gate to source leak current | I _{GSS} | _ | _ | ±10 | μΑ | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$ | |
| Zero gate voltage drain current | I _{DSS} | _ | | -100 | μΑ | $V_{DS} = -240 \text{ V}, V_{GS} = 0$ | |
| Gate to source cutoff voltage | $V_{GS(off)}$ | -2.0 | | -4.0 | V | $I_{D} = -1 \text{ mA}, V_{DS} = -10 \text{ V}$ | |
| Static drain to source on state resistance | R _{DS(on)} | _ | 6.0 | 8.5 | Ω | $I_D = -0.5 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$ | |
| Forward transfer admittance | y _{fs} | 0.25 | 0.4 | _ | S | $I_D = -0.5 \text{ A}, V_{DS} = -20 \text{ V}^{*1}$ | |
| Input capacitance | Ciss | _ | 235 | _ | pF | $V_{DS} = -10 \text{ V}, V_{GS} = 0,$ | |
| Output capacitance | Coss | _ | 65 | _ | pF | f = 1 MHz | |
| Reverse transfer capacitance | Crss | _ | 16 | _ | pF | | |
| Turn-on delay time | t _{d(on)} | _ | 10 | _ | ns | $I_D = -0.5 \text{ A}, V_{GS} = -10 \text{ V},$ | |
| Rise time | t _r | _ | 25 | _ | ns | $R_L = 60 \Omega$ | |
| Turn-off delay time | t _{d(off)} | _ | 35 | _ | ns | | |
| Fall time | t _f | _ | 45 | _ | ns | | |
| Body to drain diode forward voltage | V_{DF} | _ | -0.9 | _ | V | $I_F = -1 A, V_{GS} = 0$ | |
| Body to drain diode reverse recovery time | t _{rr} | _ | 200 | _ | ns | $I_F = -1 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$ | |

Note: 1. Pulse test



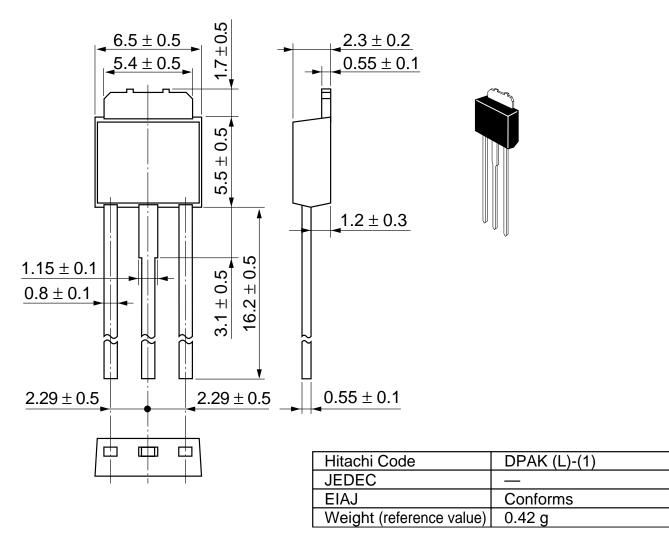






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Unit: mm



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